

Programme

Tuesday 2nd April

Registration Floor 2; 13.00 onwards

Welcome Address Stanley Thomas Lecture Theatre; 13.55 – 14.00

Session 1: Growth and Materials Stanley Thomas Lecture Theatre; 14.00 – 16.00

Refreshment Break 16.00 – 16.30; CSL, 4th Floor

Session 2: Light Emitters Stanley Thomas Lecture Theatre; 16.30 – 17.30

Break and walk to venue 17.30 – 17.45

Session 3: Poster Session (including buffet and drinks) sponsored by IOP

Semiconductors and Compound Semiconductor Centre

Transitional Research Hub; 17.45 – 19.45

Wednesday 3rd April

Session 4: Detectors Stanley Thomas Lecture Theatre; 08.30 – 10.00

Session 5: Facilities Stanley Thomas Lecture Theatre; 10.00 – 10.20

Refreshment Break 10.20 – 11.00; CSL, 4th Floor

Session 6: Moving Towards Integration Stanley Thomas Lecture Theatre; 11.00 – 13.00

Lunch 13.00 – 12.00; 4th Floor

Session 7: Material Characterisation Stanley Thomas Lecture Theatre; 14.00 – 15.00

Refreshment Break 15.00 – 15.30, 4th Floor

Session 8: Lasers and Applications I Stanley Thomas Lecture Theatre; 15.30 - 17.00

Careers Session 4th Floor, 17.00 - 18.30

Walk to venue Break 18.30-18.45

Conference Banquet Reception, The Cornerstone; 18.45 – 19.45

Conference Banquet, The Cornerstone ;19.45 Onwards

Thursday 4th April

Session 9: Lasers and Applications II Stanley Thomas Lecture Theatre; 09.00 – 10.00

Refreshment Break 10.00 – 10.30, 4th Floor

Session 10: Lasers and Applications III Stanley Thomas Lecture Theatre; 10.30 – 12.30

Lunch 12.30 – 13.30; 4th Floor

End of conference



Programme, Tuesday 2nd April

Registration

Centre for Student Life, Stanley Thomas Lecture Theatre; 13.00 onwards

Welcome Address

Centre for Student Life, Stanley Thomas Lecture Theatre; 13.55 – 14.00

Session 1: Growth and Materials

Centre for Student Life, Stanley Thomas Lecture Theatre; 14.00 – 16.00

14.00 S24_29 Antiphase boundary-free III-V materials epitaxially grown on on-axis Si (001) substrate by thin Si buffer

X Zhang*, H Jia, H Deng, H Liu and M Tang

Department of Electronic and Electrical Engineering, University College London, Torrington Place, London, WC1E 7JE, United Kingdom

14.15 S24_30 **Molecular Beam Epitaxy Growth of GaAs and Ge Buffers on V-Groove Si** M Mtunzi^{1*}, H Jia¹, Y Hou^{2,6}, X Yu¹, H Zeng¹, J Yang¹, I Skandalos², W Li³, K El Hajraoui⁴, Q Ramasse⁴, M.G Masteghin⁵, F Gardes², M Tang¹, S Chen¹ and H Liu¹

¹Department of Electronic and Electrical Engineering, University College London, Torrington Place, London WC1E 7JE, United Kingdom. ² Optoelectronics Research Centre, University of Southampton, Southampton, SO17 1BJ, United Kingdom. ³Beijing Key Lab of Microstructure and Property of Advanced Materials, Faculty of Materials and Manufacturing, Beijing University of Technology, Beijing 100124, People's Republic of China. ⁴SuperSTEM, SciTech Daresbury Science and Innovation Campus, Block J, Keckwick Lane, Daresbury, WA4 4AD, United Kingdom. ⁵Department of Electrical and Electronic Engineering, University of Surrey, Guildford, Surrey, GU2 7XH, United Kingdom

14.30 S24_05 **MOCVD** growth of InAs/GaSb Type-II superlattices for infrared detectors R Brown¹, C Liu^{1,2}, K.M Wong¹, J.I Davies², Q Li^{1*}

¹School of Physics and Astronomy, Cardiff University, United Kingdom ²IQE plc. Cardiff, Wales, CF3 0LW, United Kingdom

14.45 S24_20 **Optical properties of GaAs1-xBix MQW and InxGa1-xAs MQW structures** N.A. Adham, F Harun*, J.P.R David and R.D Richards *University of Sheffield (UK)*, **UniKL BMI (Malaysia)*

15.00 S24_27 Optoelectronic properties of Al_xGa_{1-x}As_ySb_{1-y} on GaSb



S.W Zhao¹, X Jin¹, A.P Craig², A.R.J Marshall², X Yi³, M Modak³, G.S Buller³, C Hing Tan¹ and J.P.R David¹

¹ Department of Electronic and Electrical Engineering, University of Sheffield, Sheffield S1 3JD, United Kingdom. ² Physics Department, University of Lancaster, Lancaster, LA1 4YB, United Kingdom. ³ School of Engineering & Physical Sciences, Heriot-Watt's University, Edinburgh, EH14 4AS, United Kingdom

15.15 S24_17 Effective dislocation filter layers for epitaxial growth of InP on silicon B-P Ratiu¹, S Liu¹, H Jia² and Z Yan¹

¹School of Physics and Astronomy, Cardiff University, UK. ²Dept. of Electronic & Electrical Engineering, University College London, UK. ³Univ. Grenoble Alpes, CNRS, CEA-LETI, MINATEC, LTM, F-38054 Grenoble, France

15.30 S24_34 Optically active InAs/InAlGaAs/InP (001) quantum dot laser materials enhanced by cyclic defect annealing

C Dear¹, H Jia¹, J-S Park¹, K El Hajraoui², J Yuan¹, H Deng¹, M Tang¹, Q Ramasse² and H Liu¹

¹Department of Electronic and Electical Engineering, University College London, London ²SuperSTEM, Daresbury

15.45 S24_10 Molecular beam epitaxy of AlGaN alloys with compositional fluctuations: Development of wavelength-switchable ultraviolet light emitting diodes

P.G Roy¹, S Sen² and Anirban Bhattacharyya¹

¹Institute of Radio Physics and Electronics, University of Calcutta, Kolkata 700009, INDIA. ²Centre for Research in Nanoscience and Nanotechnology, University of Calcutta, Kolkata 700106, INDIA

Refreshment break 16.00- 16.30; 4th Floor

Session 2: Light Emitters

Centre for Student Life, Stanley Thomas Lecture Theatre; 16.30 – 17.30

16.30 S24_38 Advances in Room-Temperature Single-Photon LEDs Using GaSb/GaAs Quantum Rings

G Acar¹, L Leguay², S Jones¹, P Hodgson¹, A Schliwa², M Hayne¹

¹Department of Physics, Lancaster University, Lancaster LA1 4YB, UK. ²Institute of Solid-State Physics, Technical University of Berlin, Berlin 10623, Germany

16.45 S24_08 Eco-Friendly Colloidal Quantum Dots Light Emitting Diode Arrays with Microscale Pixel Patterning through Non-Lithographic Processes

R Liu, C Kant, J Hong, O Diyar, S William, O Alexander, and B Hou School of Physics and Astronomy, Cardiff University, Cardiff CF24 3AA, United Kingdom

17.00 S24_43 Nanowire characterisation

N. Almalki

Cardiff School of Physics and Astronomy, Cardiff University, Maindy Road, Cardiff CF24 4HQ

17.15 S24_37 Novel GaSb Quantum Ring Light Emitting Diodes (QR-LED) with Distributed Bragg Transmitter (DBT) Operating at Telecommunication Wavelength



G Acar*¹, S Jones¹, P Hodgson¹, F Alvarado-Cesar², R Beanland² and M Hayne¹
¹Department of Physics, Lancaster University, Lancaster LA1 4YB, UK. ²Department of Physics, University of Warwick, Coventry CV4 7AL, UK

Break and walk to venue

Session 3: Posters & Reception Sponsored by Compound Semiconductor Centre and IOP Semiconductor

Spark, 17.45 – 19.45

S24_12 Towards Four Wave Mixing in Silicon Waveguides Using Distributed Bragg Reflector Cavities for Quantum Applications

S Bala, J Blatcher, J Pugh and M Cryan

School of Electrical, Electronic and Mechanical Engineering, University of Bristol, Woodland Road, Bristol, United Kingdom, BS8 1UB

S24_35 Emission Polarisation Switching in Single CuInZnS3 Quantum Dots

N Alhazmi, V Singh, O Evans, A Stewart, W Solari, A Osypiw, B Hou, and W Langbein School of Physics and Astronomy, Cardiff University, Cardiff CF24 2AA

S24_44 Characterisation of Silicon-Nitride Waveguides for Silicon-based Photonic Integrated Circuits of Silicon-Nitride Waveguides for Silicon-based Photonic Integrated Circuits

Yun Long¹, Pawan Mishra¹, Fwoziah Albeladi¹, Dun Qiao¹, Richard Forrest¹, Ilias Skandalos², Frederic Gardes², Peter M Smowton¹

¹ Cardiff School of Physics and Astronomy, Cardiff University, Maindy Road, Cardiff CF24 4HQ

² Optoelectronics Research Centre, University Rd, Southampton SO17 1BJ

S24 54 Laura Michael

S24_55 Joseph Francis

S24 56 Ben Jakobs

S24_57 Kate Wong



Programme, Wednesday 5th April

Session 4: Detectors

Centre for Student Life, Stanley Thomas Lecture Theatre; 08.30 – 10.30

8.30 S24_26 Characterisation of GaAs/GaAsBi heterostructure photodiodes

S Gao, X Tao, X Jin, Y Liu, N.J. Bailey, C Hing Tan, J.P R. David and R.D Richards Department of Electronic and Electrical Engineering, University of Sheffield, Sheffield, U.K

8.45 S24_42 Low excess noise Al0.75Ga0.25AsSb on InP

X Jin¹, Q Tian¹, H.I.J Lewis¹, X Yi², S Xie^{3,5}, B Liang⁴, D.L. Huffaker^{4,6}, C Hing Tan¹ and J.P. R. David¹

¹Department of Electronic and Electrical Engineering, University of Sheffield, Sheffield, S1 3JD, UK. ² Institute of Photonics and Quantum Sciences, Heriot-Watt University, Edinburgh, EH14 4AS, UK. ³ School of Physics and Astronomy, Cardiff University, Cardiff, CF24, UK. ⁴ California NanoSystems Institute, University of California, Los Angeles, California, 90095, USA. ⁵ Microsemi ltd, Shanghai, 200001, China (Present address). ⁶ Electrical Engineering Department, The University of Texas at Arlington, Texas, USA (Present address)

9.00 S24_29 Etch depth dependence on the dark current density of long-wave infrared InAs/GaSb photodiode

P O'Dowd Phanis*1, D Kwan^{1,2}, C Maxey², M Kesaria¹

¹School of Physics and Astronomy, Cardiff University, the Parade, Cardiff, CF24 3AA, UK, Present address: ²Leonard UK, First Avenue, Millbrook Industrial Estate, Southampton SO15 0LG.

9.15 S24_09 Infrared photodetectors based on pBn InGaAs/GaAsSb type-II superlattice on InP for detection in extended wavelength range

P Cao a, b, H Peng a, b, T Wang a, b, W Zheng a, b, N Davison c and Q Zhuangc

^a Laboratory of Solid-State Optoelectronics Information Technology, Institute of Semiconductors, Chinese Academy of Sciences, Beijing 100083, China. ^b State Key Laboratory on Integrated Optoelectronics, Institute of Semiconductors, Chinese Academy of Sciences, Beijing 100083, China. ^c Physics Department, Lancaster University, Lancaster UK LA1 4YB

9.30 S24_03 ITO Bolometer with Metamaterial Perfect Absorber

K.J. Thornton*, P Dong, S.F.J. Blair, J.S. Male, C.P. Reardon, Y Wang and T.F. Krauss *Photonics Research Group, School of Physics, Engineering and Technology, University of York, York, YO10 5DD*

9.45 S24_18 Colloidal quantum dots photovoltaic light-emitting field-effect transistors H Ji, P.M. Smowton and B Hou

School of Physics and Astronomy, Cardiff University, Cardiff CF24 3AA, United Kingdom

Session 5: Facilities

Centre for Student Life, Stanley Thomas Lecture Theatre; 10.00 – 11.00

10.00 S24_32 National Epitaxy Facility enabling semiconductor research in the UK Z.K. Bishop^{1*}, E. Clarke¹, E.M. Sala¹, I. Farrer¹, R.A. Oliver², H. Liu³, M.S. Skolnick⁴, and J. Heffernan¹



¹Department of Electronic and Electrical Engineering, University of Sheffield. ²Department of Materials Science and Metallurgy, University of Cambridge. ³Department of Electronic and Electrical Engineering, University College London. ⁴ Department of Physics and Astronomy, University of Sheffield

10.10 ICS

Refreshment break 10.20 – 11.00: 4th Floor

Session 6: Moving Towards Integration

Centre for Student Life, Stanley Thomas Lecture Theatre; 11.00 – 13.00

11.00 S24_36 Optimisation of photonic crystal slab cavities for high Q-factor at target eigenfrequencies

A Nilabha*, N Monima, W Langbeinb and F Masia

^aSchool of Biosciences, Cardiff University, Cardiff CF10 3AT. ^b School of Physics and Astronomy, Cardiff University, Cardiff CF10 3AT

11.15 S24_07 Towards the fabrication of a Phase Change Material (PCM)-based phase shifter: Simulation, Design, and Fabrication

A Shoaa, F Gardes, I Zeimpekis, T.D Bucio and M Banakar

Optoelectronics Research Centre, University of Southampton, Southampton SO17 1BJ, UK

11.30 S24_11 Design of a C-band InP based Mach-Zehnder Modulator

Z Chen^{1,2}*, C.E Smith¹, V Rodrigues¹, X Dai¹, P Pagnod-Rossiaux¹

¹ 3SP Technologies, Route de Villejust, 91625 Nozay Cedex, France. ² LTCI, Télécom Paris, Institut Polytechnique de Paris, 19 place Marguerite Perey, Palaiseau, 91120, France. ³ Center for High Technology Materials, University of New Mexico, Albuquerque, New Mexico, USA

11.45 S24_21 Optically Controlled RF Reflective Switches

J Yang, Y Zhang and M Cryan

School of Electrical, Electronic and Mechanical Engineering, University of Bristol

12.00 S24_02 Analysis of Barrier-Well Tunnel Diodes for Improved Curvature Coefficient

C Walsh and M Missous

Department of Electrical & Electronic Engineering, The University of Manchester, *Manchester*, *M13 9PL*, *United Kingdom*

12.15 S24 06 Photonic integrated circuits for biosensing

S. Ibrahim^{1,2}, D. Davies-Armstrong^{1,2}, S. Naserikarimvand³, S. Whelan⁴, O. J. Guy³, A. J. Bennett^{1,2}, J. P. Hadden^{1,2}

¹School of Engineering, Cardiff University, Queens Building, The Parade, Cardiff, CF24 3AA, UK. ²Translational Research Hub, Cardiff University, Maindy Road, Cathays, Cardiff, CF24 4HQ, UK. ³Department of Chemistry, School of Engineering and Applied Sciences, Faculty of Science and Engineering, Swansea University, Swansea SA2 8PP, UK.

12.30 S24_46 Achieving Reduced Absorption for Low Loss Passive Photonics Components by Using Ion Implantation



Abigail Enderson¹, Pawan Mishra¹, Lydia Jarvis¹, Fwoziah Albeladi¹, Sara-Jayne Gillgrass¹, Nianhua Peng², Mingchu Tang³, Huiyun Liu³, Samuel Shutts¹, and Peter M. Smowton¹

¹ School of Physics and Astronomy, Cardiff University, The Parade, Cardiff. CF24 3AA. United Kingdom.

12.45 S24_24 A study of the effects of Micro-Transfer Printing on the Performance of SAM Avalanche Photodiodes

YAlimi¹, B Guilhabert² and M Strain²

¹Department of Electronic and Electrical Engineering, University of Sheffield, Sheffield, S1 3JD, UK. ²Institute of Photonics, Dept. of Physics, University of Strathclyde, Technology and Innovation Centre, 99 George Street, Glasgow, G1 1RD

Lunch 13.00 – 14.00; 4th Floor

Session 7: Material Characterisation

Centre for Student Life, Stanley Thomas Lecture Theatre; 14.00 – 15.00

14.00 S24_47 QuickSELs Enabling Rapid Feedback to Epitaxy

J. Baker¹, C. P. Allford¹, S. Gillgrass¹, J. I. Davies², S. Shutts¹, P. M. Smowton^{1,3}

14.15 S24_31 Time-of-Flight Elastic Recoil Detection Analysis and Rutherford Backscattering Spectrometry to Characterise AlxGa1-xAs1-yBiy Avalanche Photodetectors

C. McAleese¹, M. K. Sharpe¹, M. R. Carr², J. P. R. David² and R. D. Richards¹

¹Ion Beam Centre, Advanced Technology Institute, University of Surrey, Guildford, GU2 7XH, UK. ² Electronic and Electrical Engineering Department, The University of Sheffield, Sheffield, S1 3JD, UK

14.30 S24_04 Extended defects characterisation of 50 mm GaN wafer using electron channelling contrast imaging in a scanning electron microscope

K. Nicholson¹, D. Muir² and N. Gunasekar¹

14.45 S24 14 Holographic measurement of the gain of semiconductor waveguides

L. Zens, V. Besaga, J. Möller, N. C. Gerhardt, and M. R. Hofmann

¹Ruhr-University Bochum, Universitaetsstr. 150, 44801 Bochum, Germany. ² Friedrich Schiller Universität Jena, Abbe Center of Photonics, Albert-Einstein-Straβe 6, 07745 Jena, Germany

Refreshment break 15.00 – 15.30; 4th Floor

² Surrey Ion Beam Centre, University of Surrey, Guildford, Surrey, United Kingdom.

³ Department of Electrical Engineering, University College London, London, United Kingdom.

¹ Future Compound Semiconductor Manufacturing Hub, Cardiff University, UK.

² IQE plc, Cardiff, UK.

³ Institute for Compound Semiconductors, Cardiff University, UK.

¹ School of Physics and Astronomy, Cardiff University, Cardiff CF24 3AA, United Kingdom

² School of Earth and Environmental Sciences, Cardiff University, Cardiff CF10 3AT, United Kingdom



Session 8: Lasers and Applications I

Centre for Student Life, Stanley Thomas Lecture Theatre; 15.30 – 17.00

15.30 S24_13 Room Temperature Lasing from GaAs/InGaAs/InGaP Quantum Well Nanowires

B Temu, Z Yan, B-P Ratiu, K. M Wong, S Soon Oh and Q Li School of Physics and Astronomy, Cardiff University, United Kingdom

15.45 S24_48

M. Alsayyadi

EPSRC Future Compound Semiconductor Manufacturing Hub, School of Physics and Astronomy, Cardiff University, Cardiff, UK, CF24 3AA

16.00 S24_16 Optimizing Distributed-Feedback Quantum Cascade Lasers: Comprehensive Insights into Spatial Hole Burning and Linewidth Enhancement Factor Impact

S. Zaminga^{1*}, L. Columbo², C. Silvestri³, M. Gioannini², and F. Grillot^{1,4}

¹LTCI Télécom Paris, Institut Polytechnique de Paris, Palaiseau, 91120, France. ² Dipartimento di Elettronica e Telecomunicazioni, Politecnico di Torino, Torino, Italy. ³ School of Electrical Engineering and Computer Science, The University of Queensland, Brisbane, Australia. ⁴ Center for High Technology Materials, University of New-Mexico, Albuquerque, NM 87106, USA

$\textbf{16.15} \ \ S24_15 \ \ \textbf{Mid-Infrared InAs/GaInSb} \ \ \textbf{W-Quantum Well based Interband Cascade Lasers}$

M. Bentley*¹, P. Ghosh¹, P. J. Carrington², Q. Zhuang¹

¹Department of Physics, Lancaster University, LA1 4YB. ²School of Engineering, Lancaster University, LA1 4YW

16.30 S24_23 Hybrid Integration of Mid-IR Quantum Cascade Lasers on Ge-on-Si Platform

L Zhou¹, K M Groom¹, D.G Revin¹, C.J Mitchell², G Mashanovich², J Heffernan¹

¹Department of Electronic and Electrical Engineering, University of Sheffield, Sheffield, S1 3JD, UK. ²Optoelectronics Research Centre, University of Southampton, Southampton, SO17 1BJ, UK

16.45 S24_22 Diode Area Melting and the Opportunities for Advanced Optoelectronics in Additive Manufacturing

K Groom¹, S. Veetil¹, Z. Zhang¹, L. Zhou¹, J. Willmott¹, I. Wraith¹, M. Alsaddah², A. Aydin², A.Liang², R. Brown², H. Caglar², C. Majewski², K. Mumtaz²

¹Dept. of Electronic & Electrical Engineering, University of Sheffield, S1 3JD. ²Dept. of Mechanical Engineering, University of Sheffield, S1 3J

Break and walk to venue

Conference Banquet Reception

The Conerstone 18.45 - 19.45

Conference Banquet



The Conerstone; 19.45 onwards



Programme, Thursday 4th April

Session 9: Lasers and Applications II

Centre for Student Life, Stanley Thomas Lecture Theatre; 9.00 – 10.30

9.00 S24_49 High Temperature Operation of O-band InAs Quantum Dot Laser

Pawan Mishra¹, Lydia Jarvis¹, Chris Hodges¹, Abigail Enderson¹, Fwoziah Albeladi¹, Sara-Jayne Gillgrass¹, Richard Forrest¹, Craig P. Allford¹, Mingchu Tang², Huiyun Liu², Samuel Shutts¹, and Peter M. Smowton¹

09.15 S24_50 Improving the performance of p-doped QD lasers and modulators

L Jarvis¹, B.C. Maglio², F Albeladi¹, S-J Gillgrass¹, C.P. Allford¹, MTang³, H Liu³, S Shutts¹, and P.M. Smowton^{1,*}

¹. School of Physics and Astronomy, Cardiff University, The Parade, Cardiff. CF24 3AA. United Kingdom. ². Institute of Arctic Biology, University of Alaska Fairbanks, Fairbanks, AK 99775, United States of America. ³. Department of Electrical Engineering, University College London, London, United Kingdom.

09.30 S24_25 1.3 μm Optically Pumped Quantum Dot Photonic Crystal Laser Designed at Bounded States in the Continuum

D. Lei, J Wang, N. C. Panoiu, H Liu

Department of Electronic and Electrical Engineering, University College London, Torrington Place, London WC1E 7JE, U.K

9.45 S24 52 1390nm Dilute Nitride VCSELs on 150mm GaAs

I.F Obuseli¹, C.P Allford¹, S. Gillgrass¹, A. Clark³, K. Nunna³, J.I Davies² and P.M Smowton¹ EPSRC Future Compound Semiconductor Manufacturing Hub, School of Physics and Astronomy, Cardiff University, Cardiff, UK, CF24 3AA

10.00 S24_41 GaSb/GaAs Quantum-Ring Vertical-Cavity Surface-Emitting Lasers Approaching 1.3-µm Emission

S. Jones, P. D. Hodgson, and M. Hayne

Department of Physics, Lancaster University, Lancaster LA1 4Y

10.15 S24_28 Bidirectional Widely Tuneable 1310 nm MEMS VCSEL

M Payandeh *, H.K Sahoo and E Semenova

Department of Electrical and Photonic Engineering, Technical University of Denmark, 2800 Kgs. Lyngby, Denmark

¹ School of Physics and Astronomy, Cardiff University, The Parade, Cardiff. CF24 3AA. United Kingdom.

² Department of Electrical Engineering, University College London, London, United Kingdom.

² IQE NC, Gallimore Dairy Road, Greensboro, NC 27409, USA

³ IQE plc, Pascal Close, St. Mellons, Cardiff, UK, CF3 0LW



Refreshment break 10.30 – 11.00; 4th Floor

Session 10: Lasers and Applications III

Centre for Student Life, Stanley Thomas Lecture Theatre; 11.00 – 12.30

11.00 S24_52 1st Order Gratings for Laterally Coupled DFB lasers Fabricated with E-Beam and Focused Ion Beam Lithography

B. Salmond¹, T. Peach², D. Read^{1,3}, D. John³, B. Mitchell³, B. Thibeault³, T. Richter⁴, A. Nadzeyka⁴, P. Mazarov⁴, F. Meyer⁴, J. Fridmann⁴, Y. Yu⁴, W. Meredith⁵, M. Wale⁶, P. Smowton^{1,2} and S.Shutts^{1,2}

¹School of Physics and Astronomy, Cardiff University, Cardiff CF24 3AA, UK. ²Institute for Compound Semiconductors (ICS), Translational Research Hub, Maindy Road, Cardiff CF24 4HQ, UK. ³Department of Electrical and Computer Engineering, University of California Santa Barbara, Santa Barbara, CA 93106, USA. ⁴Raith GmbH, Konrad-Adenauer-Allee 8, 44263 Dortmund, Germany. ⁵Compound Semiconductor Centre Ltd, St Mellons, Cardiff CF3 0LW. ⁶Department of Electronic and Electrical Engineering, University College London, London WC1E 7JE

11.15 S24_53 Thermal Performance of VCSELs on Germanium Substrates

J. Baker¹, C. P. Allford¹, S. Gillgrass¹, J. I. Davies², S. Shutts¹, P. M. Smowton^{1,3}

11.30 S24_33 **Semiconductor Lasers Subject to Frequency Modulated Optical Injection** K. A. Shore ⁽¹⁾ ,Y. Fan ⁽²⁾ and Y.Hong(¹⁾

(1) Bangor University, School of Computer Science and Electronic Engineering, LL57 1UT, Wales, UK. (2) Hangzhou Institute of Technology, Xidian University, Hangzhou, 311200, China;

11.45 S24_30 Time-dependent flip-flop spiking memory in RTD neurons

G. Donati*, D. Owen-Newns, J. Robertson and A. Hurtado

Institute of Photonics, Dept. of Physics, University of Strathclyde, Glasgow, UK

12.00 S24_01 Chaos-Based Photonic Information-Processing Platforms: Capabilities and Challenges

K. A. Shore ⁽¹⁾, P. Li ^(2,3) and Y. C. Wang ⁽²⁾

(1) Bangor University, School of Computer Science and Electronic Engineering, LL57 1UT, Wales, UK (2) Guangdong Provincial Key Laboratory of Photonics Information Technology, School of Information Engineering, Guangdong University of Technology, Guangzhou 510006, China (3) Key Laboratory of Advanced Transducers and Intelligent Control System, Ministry of Education, Taiyuan University of Technology, Taiyuan

12.15 S24_19 Optical VCSEL-based Spiking Neural Networks for High-Speed Target Detection and Tracking

J. Robertson, ¹* P. Kirkland, ² G. Di Caterina, ² and A. Hurtado ¹

¹Institute of Photonics, Dept. of Physics, University of Strathclyde, Glasgow, UK, ²Dept of Electronic and Electrical Engineering, University of Strathclyde, Glasgow, UK

¹ Future Compound Semiconductor Manufacturing Hub, Cardiff University, UK.

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Conference Ends